

11A, 60V, 0.107 Ohm, Logic Level, N-Channel Power MOSFETs

These N-Channel enhancement-mode power MOSFETs are manufactured using the latest manufacturing process technology. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49158.

Ordering Information

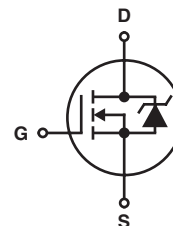
PART NUMBER	PACKAGE	BRAND
RFD3055LE	TO-251AA	F3055L
RFD3055LESM	TO-252AA	F3055L
RFP3055LE	TO-220AB	FP3055LE

NOTE: When ordering, use the entire part number. Add the suffix, 9A, to obtain the TO-252 variant in tape and reel, e.g. RFD3055LESM9A.

Features

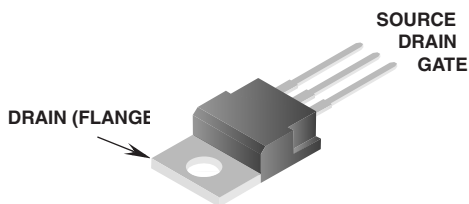
- 11A, 60V
- $r_{DS(ON)} = 0.107\Omega$
- Temperature Compensating PSPICE® Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

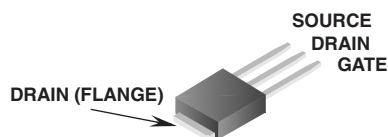


Packaging

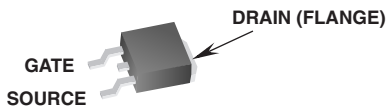
JEDEC TO-220AB



JEDEC TO-251AA



JEDEC TO-252AA



RFD3055LE, RFD3055LESM, RFP3055LE

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFD3055LE, RFD3055LESM, RFP3055LE	UNITS
Drain to Source Voltage (Note 1)	60	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	60	V
Gate to Source Voltage	± 16	V
Continuous Drain Current	11	A
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Single Pulse Avalanche Rating	Refer to UIS Curve	
Power Dissipation	38	W
Derate Above 25°C	0.25	W/ $^\circ\text{C}$
Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V		60	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA		1	-	3	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 55V, V _{GS} = 0V		-	-	1	μA
		V _{DS} = 50V, V _{GS} = 0V, T _C = 150°C		-	-	250	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±16V		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 8A, V _{GS} = 5V (Figure 11)		-	-	0.107	Ω
Turn-On Time	t _{ON}	V _{DD} ≈ 30V, I _D = 8A, V _{GS} = 4.5V, R _{GS} = 32Ω (Figures 10, 18, 19)		-	-	170	ns
Turn-On Delay Time	t _{d(ON)}			-	8	-	ns
Rise Time	t _r			-	105	-	ns
Turn-Off Delay Time	t _{d(OFF)}			-	22	-	ns
Fall Time	t _f			-	39	-	ns
Turn-Off Time	t _{OFF}			-	-	92	ns
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 10V	V _{DD} = 30V, I _D = 8A, I _{g(REF)} = 1.0mA (Figures 20, 21)	-	9.4	11.3	nC
Gate Charge at 5V	Q _{g(5)}	V _{GS} = 0V to 5V		-	5.2	6.2	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 1V		-	0.36	0.43	nC
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 14)		-	350	-	pF
Output Capacitance	C _{OSS}			-	105	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	23	-	pF
Thermal Resistance Junction to Case	R _{θJC}			-	-	3.94	°C/W
Thermal Resistance Junction to Ambient	R _{θJA}	TO-220AB		-	-	62	°C/W
		TO-251AA, TO-252AA		-	-	100	°C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 8\text{A}$		-	1.25	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 8\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$		-	66	ns

NOTES:

2. Pulse Test: Pulse Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$.
3. Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

Typical Performance Curves Unless Otherwise Specified

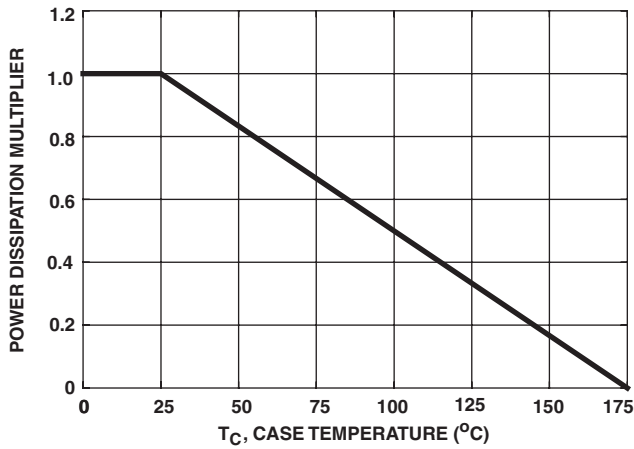


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

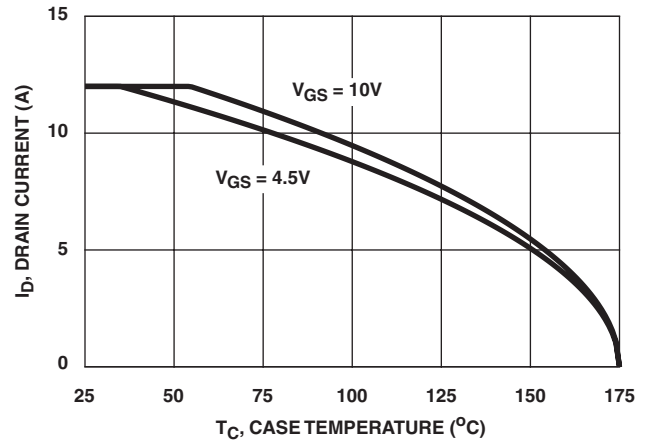


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

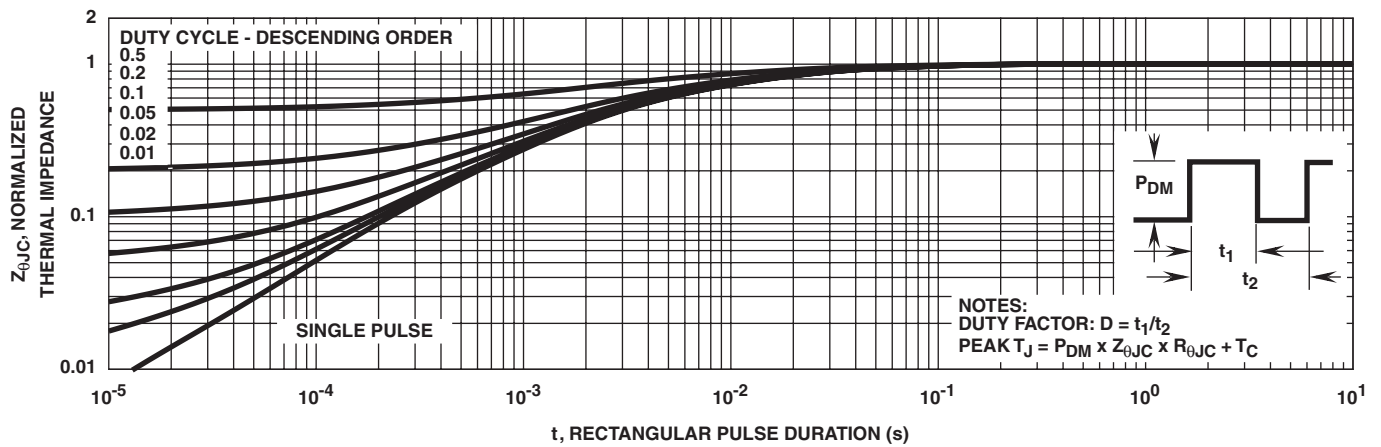


FIGURE 3. NORMALIZED TRANSIENT THERMAL IMPEDANCE

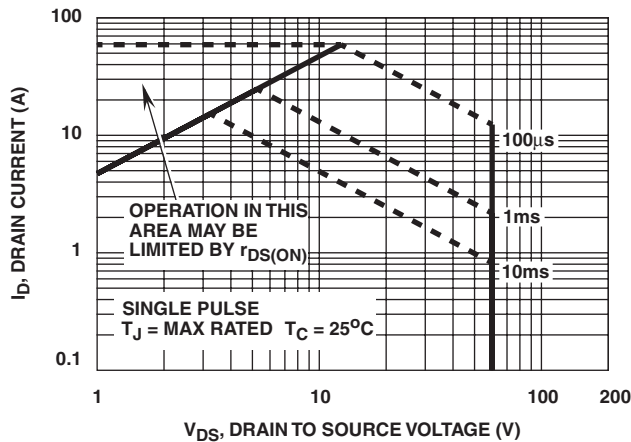


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

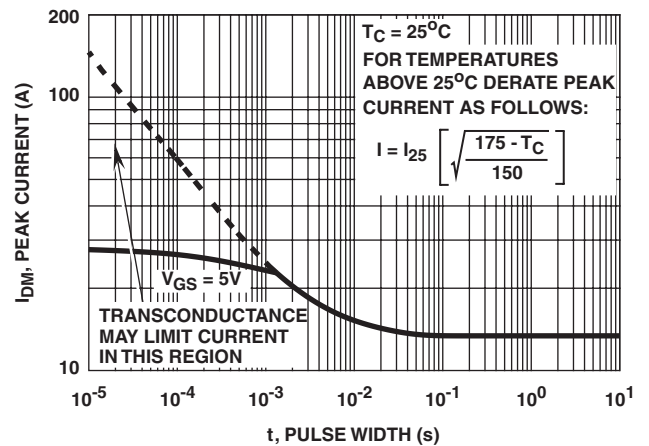
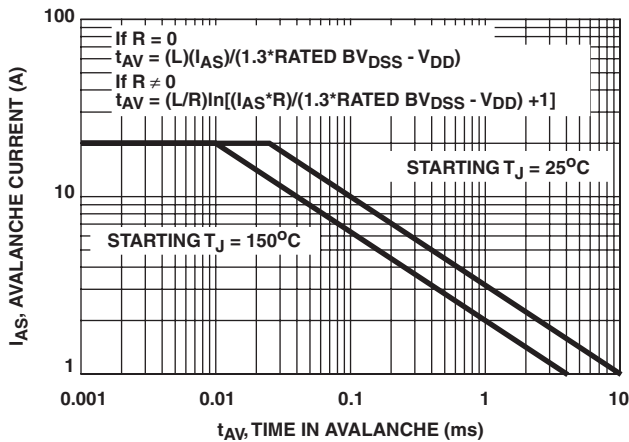


FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

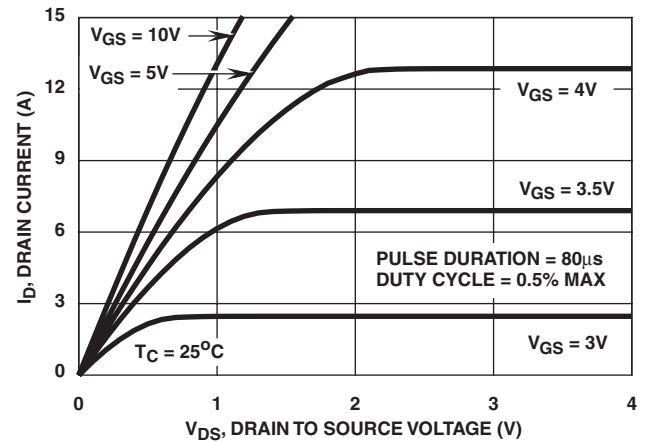


FIGURE 7. SATURATION CHARACTERISTICS

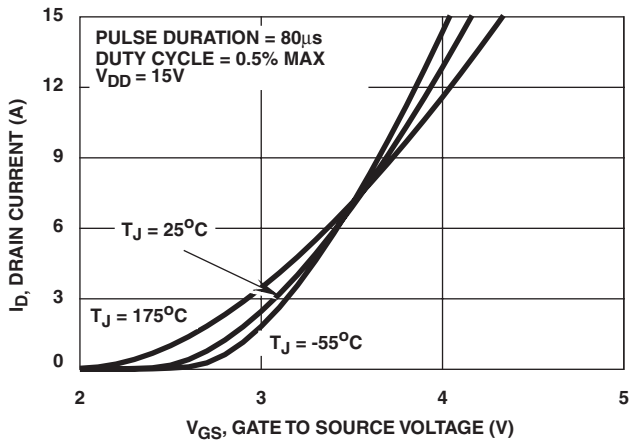


FIGURE 8. TRANSFER CHARACTERISTICS

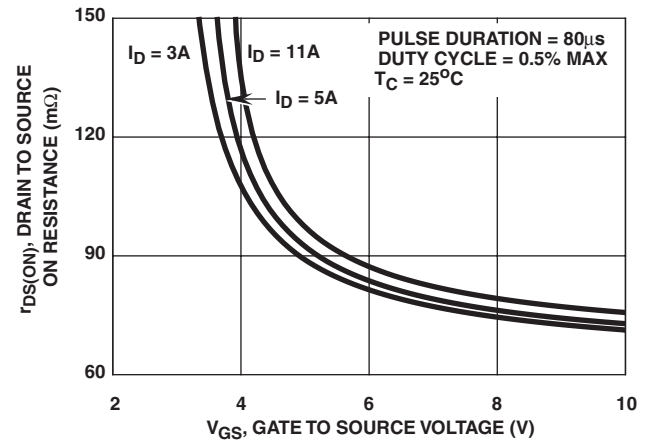


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

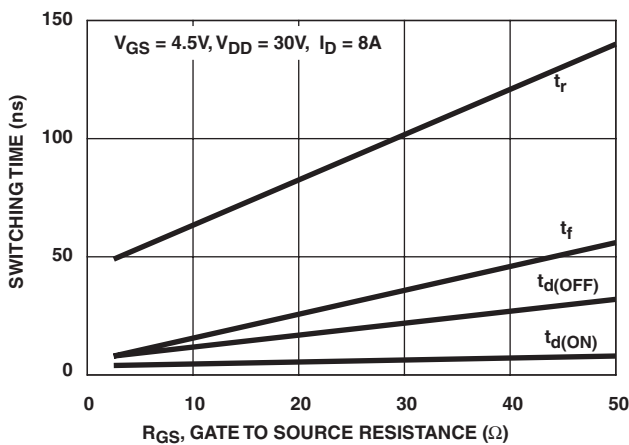


FIGURE 10. SWITCHING TIME vs GATE RESISTANCE

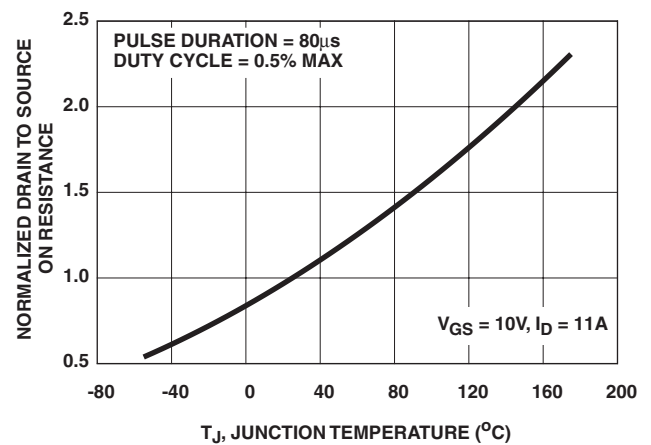


FIGURE 11. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

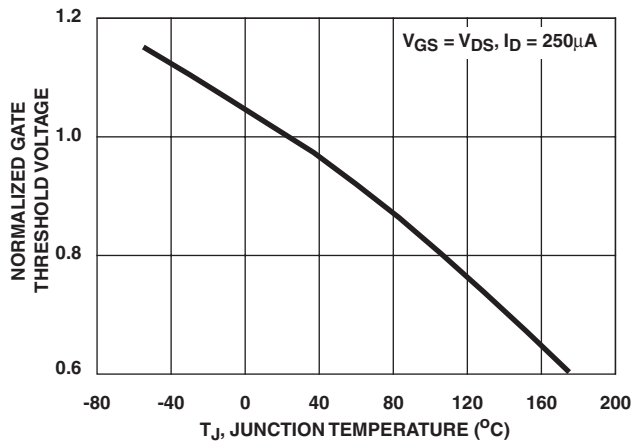


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

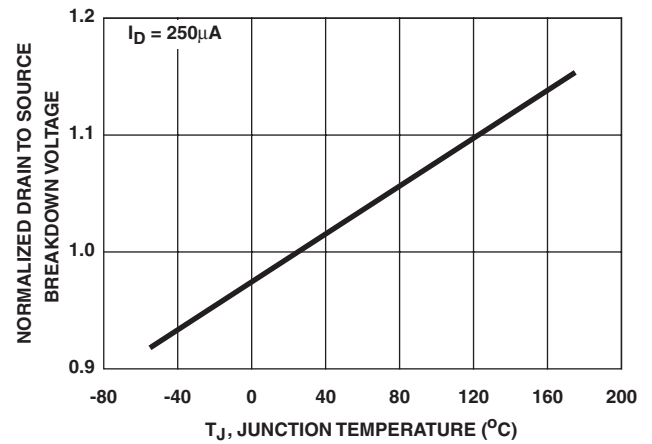


FIGURE 13. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

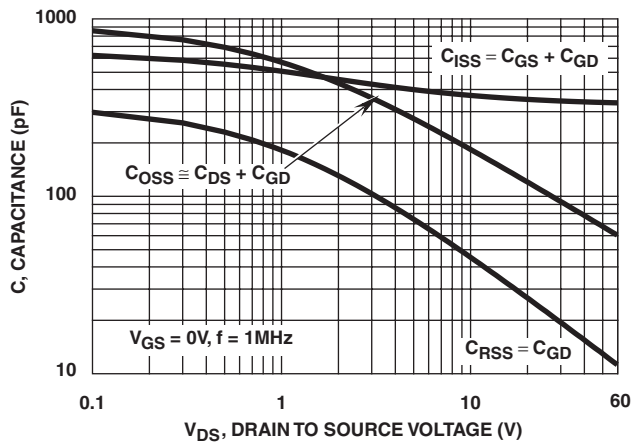
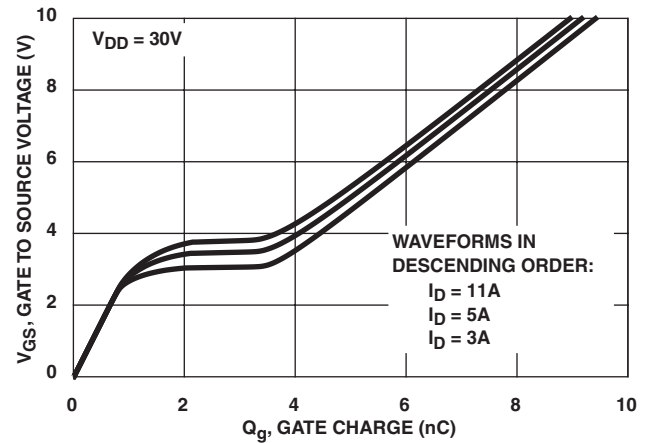


FIGURE 14. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 15. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

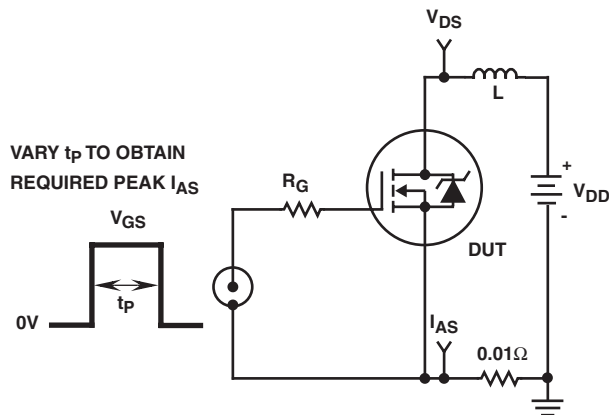


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

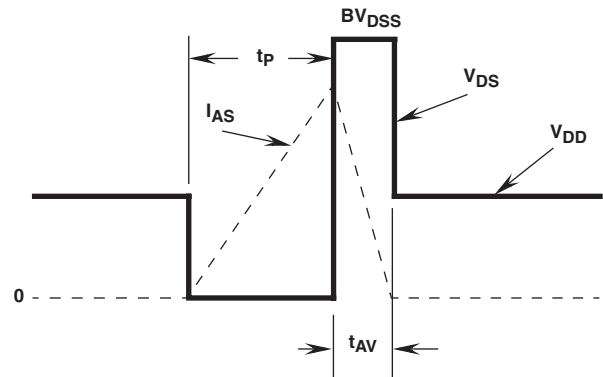


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

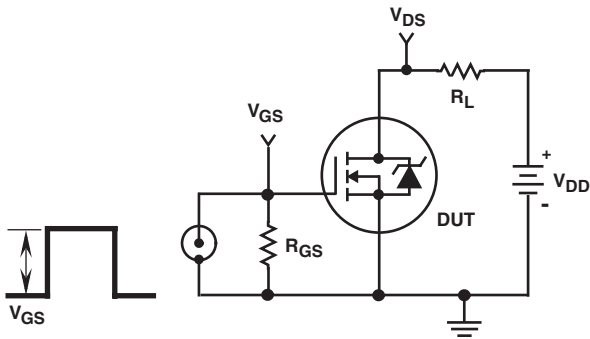


FIGURE 18. SWITCHING TEST CIRCUIT

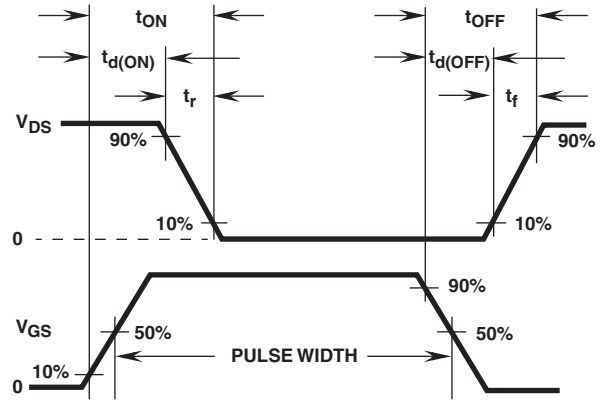


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

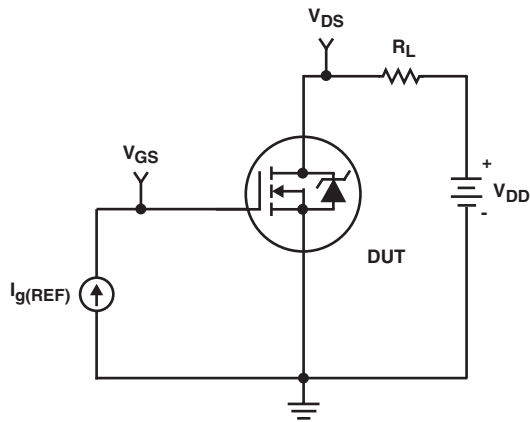


FIGURE 20. GATE CHARGE TEST CIRCUIT

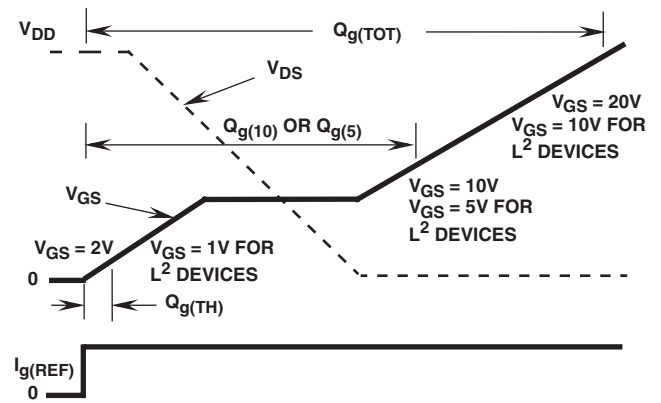


FIGURE 21. GATE CHARGE WAVEFORMS

PSICE Electrical Model

.SUBCKT RFD3055LE 2 1 3; rev 1/30/95

CA 12 8 3.9e-9
CB 15 14 4.9e-9
CIN 6 8 3.25e-10

DBODY 7 5 DBODYMOD
DBREAK 5 11 DBREAKMOD
DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 67.8
EDS 14 8 5 8 1
EGS 13 8 6 8 1
ESG 6 10 6 8 1
EVTHRES 6 21 19 8 1
EVTEMP 20 6 18 22 1

IT 8 17 1

LDRAIN 2 5 1.0e-9
LGATE 1 9 5.42e-9
LSOURCE 3 7 2.57e-9

MMED 16 6 8 8 MMEDMOD
MSTRO 16 6 8 8 MSTROMOD
MWEAK 16 21 8 8 MWEAKMOD

RBREAK 17 18 RBREAKMOD 1
RDRAIN 50 16 RDRAINMOD 3.7e-2
RGATE 9 20 3.37
RLDRAIN 2 5 10
RLGATE 1 9 54.2
RLSOURCE 3 7 25.7
RSLC1 5 51 RSLCMOD 1e-6
RSLC2 5 50 1e3
RSOURCE 8 7 RSOURCEMOD 2.50e-2
RVTHRES 22 8 RVTHRESMOD 1
RVTEMP 18 19 RVTEMPMOD 1

S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD

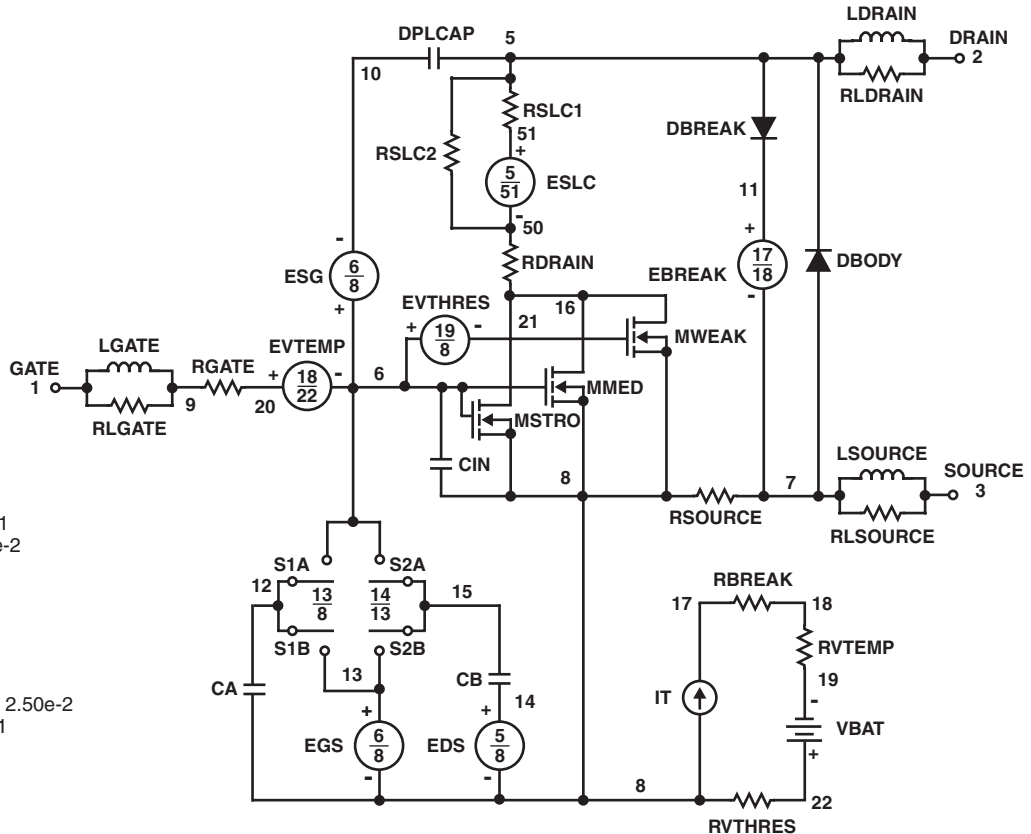
VBAT 22 19 DC 1

ESLC 51 50 VALUE=((V(5,51)/ABS(V(5,51))))*(PWR(V(5,51)/(1e-6*30),3)))

.MODEL DBODYMOD D (IS = 1.75e-13 RS = 1.75e-2 TRS1 = 1e-4 TRS2 = 5e-6 CJO = 5.9e-10 TT = 5.45e-8 N = 1.03 M = 0.6)
.MODEL DBREAKMOD D (RS = 6.50e-1 TRS1 = 1.25e-4 TRS2 = 1.34e-6)
.MODEL DPLCAPMOD D (CJO = 3.21e-10 IS = 1e-30 N = 10 M = 0.81)
.MODEL MMEDMOD NMOS (VTO = 2.02 KP = .83 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 3.37)
.MODEL MSTROMOD NMOS (VTO = 2.39 KP = 14 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL MWEAKMOD NMOS (VTO = 1.78 KP = 0.02 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 33.7 RS = 0.1)
.MODEL RBREAKMOD RES (TC1 = 1.06e-3 TC2 = 0)
.MODEL RDRAINMOD RES (TC1 = 1.23e-2 TC2 = 2.58e-5)
.MODEL RSLCMOD RES (TC1 = 0 TC2 = 0)
.MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 0)
.MODEL RVTHRESMOD RES (TC1 = -2.19e-3 TC2 = -4.97e-6)
.MODEL RVTEMPMOD RES (TC1 = -1.6e-3 TC2 = 1e-7)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -4 VOFF = -2.5)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.5 VOFF = -4)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.5 VOFF = 0)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0 VOFF = -0.5)

.ENDS



For further discussion of the PSICE model, consult **A New PSICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^{Ex} TM	FAST [®]	OPTOLOGIC TM	SMART START TM	VCX TM
Bottomless TM	FAST ^r TM	OPTOPLANAR TM	STAR*POWER TM	
CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.